

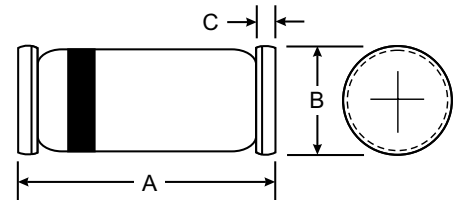


Features

- Silicon Planar Diodes
- Very low reverse current

Mechanical Data

- Case: SOD-80/LL34, Glass
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.05 grams (approx.)



LL34/ SOD-80		
Dim	Min	Max
A	3.30	3.70
B	1.30	1.60
C	0.28	0.50
All Dimensions in mm		

Maximum Ratings @ T_A = 25°C unless otherwise specified

Parameter	Test condition	Part	Symbol	Value	Unit
Reverse voltage		BAQ33	V _R	30	V
		BAQ34	V _R	60	V
		BAQ35	V _R	125	V
Peak forward surge current	t _p = 1 μs		I _{FSM}	2	A
Forward current			I _F	200	mA

Thermal Characteristics T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction to ambient air	on PC board 50 mm x 50 mm x 1.6 mm	R _{thJA}	500	K/W
Junction temperature		T _j	175	°C
Storage temperature range		T _{stg}	- 65 to + 175	°C

Electrical Characteristics T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Forward voltage	I _F = 100 mA		V _F			1	V
Reverse current	E ≤ 300 lx, rated V _R		I _R		1	3	nA
	E ≤ 300 lx, rated V _R , T _j = 125 °C		I _R			0.5	μA
	E ≤ 300 lx, V _R = 15 V	BAQ33	I _R		0.5	1	nA
	E ≤ 300 lx, V _R = 30 V	BAQ34	I _R		0.5	1	nA
	E ≤ 300 lx, V _R = 60 V	BAQ35	I _R		0.5	1	nA
Breakdown voltage	I _R = 5 μA, t _p /T = 0.01, t _p = 0.3 ms	BAQ33	V _(BR)	40			V
	I _R = 5 μA, t _p /T = 0.01, t _p = 0.3 ms	BAQ34	V _(BR)	70			V
		BAQ35	V _(BR)	140			V
Diode capacitance	V _R = 0, f = 1 MHz		C _D			3	pF



Typical Characteristics (Tamb = 25 °C unless otherwise specified)

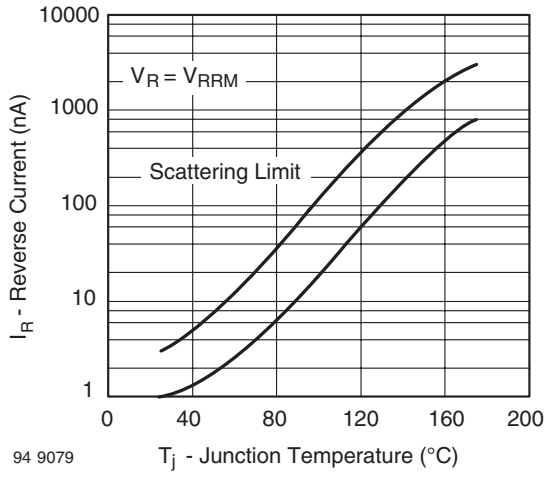


Figure 1. Reverse Current vs. Junction Temperature

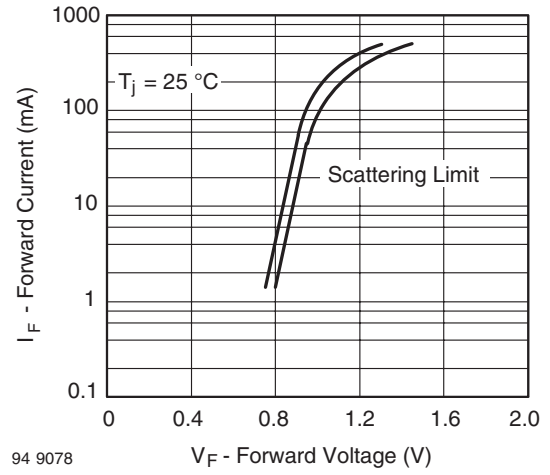


Figure 2. Forward Current vs. Forward Voltage